

APPENDIX B

The entire set of the pending claims is as follows.

18. (Amended) An apparatus for depositing a layer on a substrate, comprising:
a load lock chamber receiving a substrate having a gate wire pattern formed thereon;
a preheat chamber receiving the substrate from said load lock chamber and heating the substrate before deposition;
a deposition chamber depositing a gate insulating layer, an amorphous silicon layer and a doped amorphous silicon layer by chemical vapor deposition; and
a sputter chamber depositing a metal layer on the doped amorphous silicon layer by sputtering,
wherein the substrate is transferred from said deposition chamber to said sputter chamber in a vacuum.
22. (Newly added) A deposition apparatus, comprising:
a deposition chamber for depositing a doped amorphous silicon layer on a substrate;
a sputter chamber for depositing a metal layer on the doped amorphous silicon layer; and
a vacuum passage for transferring the substrate in a vacuum from said deposition chamber to said sputter chamber to prevent oxidization of an upper surface of the doped amorphous silicon layer.
23. (Newly added) The deposition apparatus of claim 22, wherein said deposition chamber is a CVD (chemical vapor deposition) chamber.

24. (Newly added) The deposition apparatus of claim 23, further comprising another CVD chamber for depositing a gate insulating layer, an amorphous silicon layer on the substrate prior to depositing the doped amorphous silicon layer.

25. (Newly added) The deposition apparatus of claim 24, wherein the gate insulating layer is formed at a thickness between 3000 Å to 6000 Å, the amorphous silicon layer is formed at a thickness between 1000 Å to 3000 Å, and the doped amorphous silicon layer is formed at a thickness of 200 Å to 1000 Å.

26. (Newly added) The deposition apparatus of claim 24, further comprising a preheat chamber for heating the substrate prior to depositing the gate insulating layer and the amorphous silicon layer.

27. (Newly added) The deposition apparatus of claim 24, further comprising a load lock chamber for receiving the substrate.

28. (Newly added) The deposition apparatus of claim 22, wherein the substrate has a gate wire layer formed thereon.

29. (Newly added) The deposition apparatus of claim 22, wherein the metal layer comprises chromium (Cr).

30. (Newly added) The deposition apparatus, comprising:
a load lock chamber for receiving a substrate;
a preheat chamber for heating the substrate;
a deposition chamber for depositing a doped amorphous silicon layer on the substrate;
a sputter chamber for depositing a metal layer on the doped amorphous silicon layer; and
a vacuum passage for transferring the substrate in a vacuum from said deposition chamber to said sputter chamber to prevent oxidization of an upper surface of the doped amorphous silicon layer.

31. (Newly added) The deposition apparatus of claim 30, wherein the substrate has a gate wire pattern formed thereon.

32. (Newly added) The deposition apparatus of claim 31, further comprising another deposition chamber for depositing a gate insulating layer and an amorphous silicon layer on the gate wire pattern prior to depositing the doped amorphous silicon layer.

33. (Newly added) The deposition apparatus of claim 30, wherein the deposition chamber is a chemical vapor deposition (CVD) chamber.

34. (Newly added) The deposition apparatus of claim 31, wherein the metal layer comprises chromium (Cr).